

/ Descriptions

WR0<5 M M QSQ æ M ç s ll 1 Silicon NPN transistor in a TO-92 Plastic Package.

/ Features

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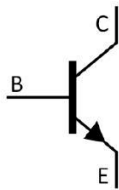
High gain, good linearity of h_{FE}.

/ Applications

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TV final picture IF amplifier applications.

/ Equivalent Circuit



/ Pinning



PIN1 χ Collector

PIN 2 χ Emitter

PIN 3 χ Base

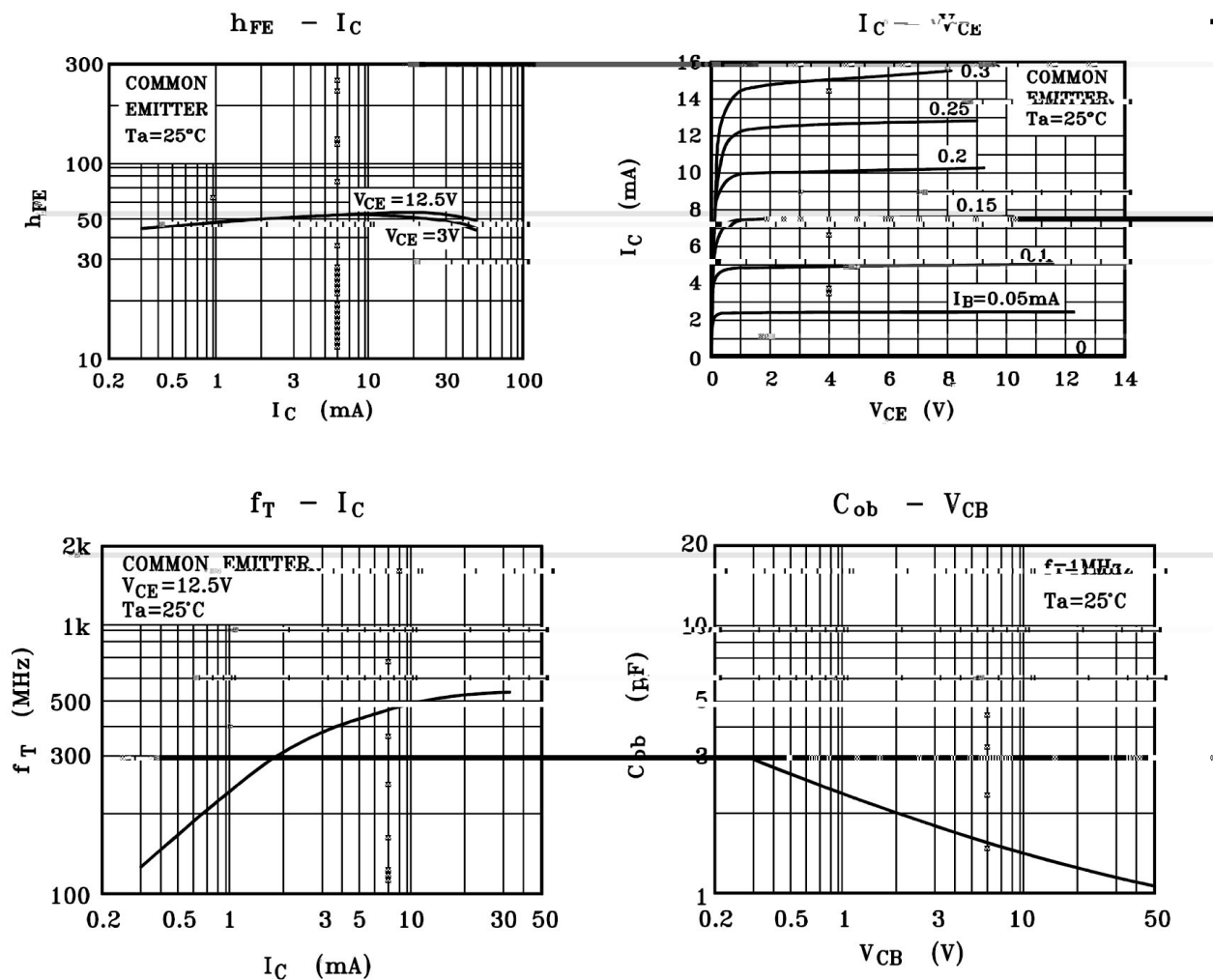
/ hFE Classifications & Marking

M ç " See Marking Instructions.

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	30	V
Collector to Emitter Voltage	V_{CEO}	25	V
Emitter to Base Voltage	V_{EBO}	4.0	V
Collector Current - Continuous	I_C	50	mA
Emitter Current - Continuous	I_E	-50	mA
Collector Power Dissipation	P_C	300	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=10mA$ $I_B=0$	25			V

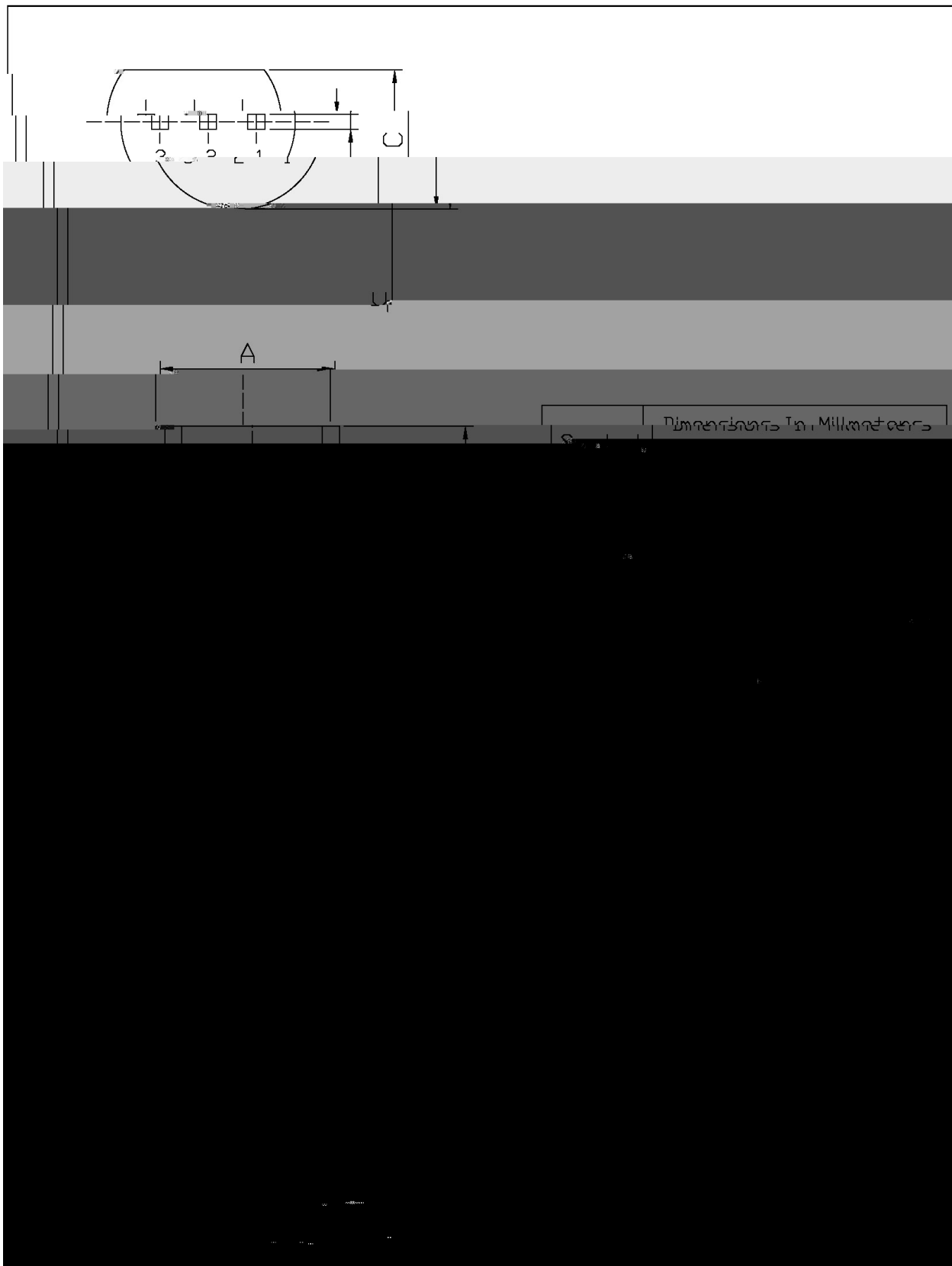
/ Electrical Characteristic Curve



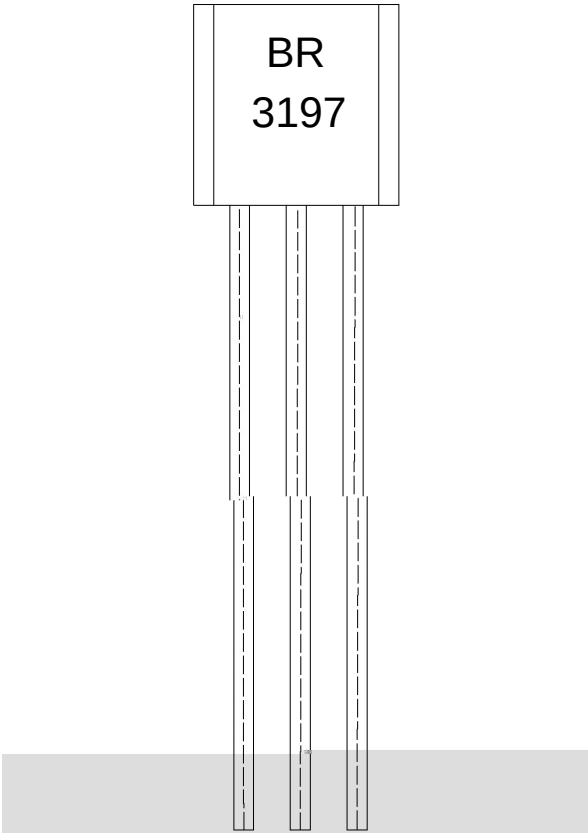
/ Package Dimensions

TO-92

Unit: mm

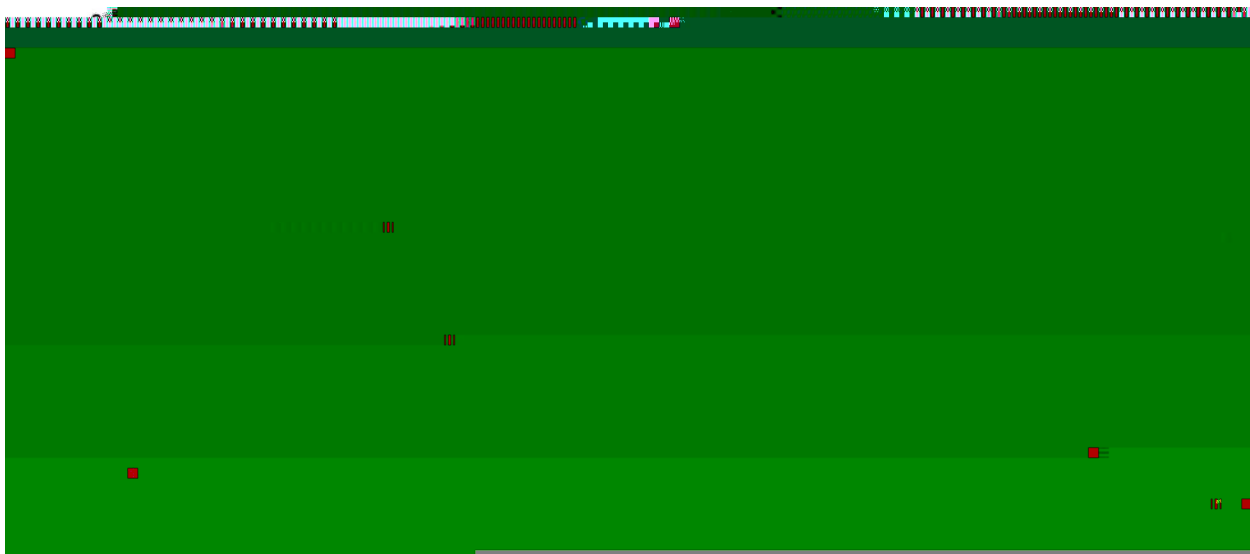


/ Marking Instructions



” X	
EU:	ꯏ ꯚ ꯍꯤ
64<: X	ꯏ ꯚ ꯍꯤ
---- X	ꯏ ꯚ ꯍ ꯈ ꯍ ꯤ ꯍꯤ ꯚ ꯚ ꯍ ꯈ ꯍ ꯚ ꯚ
Note:	
BR:	Company Code.
3197:	Product Type.
****:	Lot No. Code,code change with Lot No.

() / Temperature Profile for Dip Soldering(Pb-Free)



- ” X
1. 25~150 °C, Time: 60~90sec;
 2. 255 °C, Duration: 5~0.5sec;
 3. Cooling Speed: 2~10 °C/sec.

- Note:
1. Preheating: 25~150 °C, Time: 60~90sec.
 2. Peak Temp.: 255 °C, Duration: 5~0.5sec.
 3. Cooling Speed: 2~10 °C/sec.

/ Resistance to Soldering Heat Test Conditions

270 °C ± 5 °C, Time: 10 ± 1 sec. Temp: 270 ± 5 Time: 10 ± 1 sec

/ Packaging SPEC.

QTY / BULK